Oxford Instruments – RIE-ICP PlasmaPro 100 Cobra

- Single wafer cassette loading
- Substrate temperature control is provided by a range of electrodes, with a temperature range of -150°C to +700°C
- 12-line gas pod provides flexibility in processes and process gases
- Cryo Si etch, Bosch deep Si etch and SOI processes for MEMS, microfluidics and photonics
- Up to 200mm single wafer processing
- Available etch and process gases: BCl_3, Cl_2, H_2, Ar, N_2